CLAIM AMENDMENTS

1. (Currently Amended) A method for manufacturing a semiconductor device comprising ~~the steps of~~:

forming a first insulating film on a substrate;

forming a second insulating film on the first insulating film; and

forming a gate electrode on the second insulating film~~,~~ wherein

~~the step of~~ forming a second insulating film comprises

~~a first step of~~ supplying film-forming materials and ~~making~~ adsorbing the film-forming materials ~~adsorbed~~ on the first insulating film;

~~a second step of~~ purging the film-forming materials that ~~has~~ have not been adsorbed;

~~a third step of~~ supplying oxidants to oxidize the adsorbed film-forming materials; and

~~a fourth step of~~ purging the oxidants that ~~has~~ have not contributed to oxidization;

~~the step of~~ forming ~~a~~ the second insulating film ~~is repeated~~ repeatedly, for a plurality of cycles, continuously; and

~~the~~ purging the oxidants for a purging time ~~in the fourth step~~ in ~~the~~ an initial ~~predetermined~~ number of the plurality cycles that is ~~made~~ longer than the purging time of oxidants in the ~~fourth step in following~~ cycles after the initial number of cycles.

2. (Currently Amended) The method for manufacturing a semiconductor device according to claim 1, wherein the purging time of the oxidants in the ~~fourth step in~~ initial ~~predetermined~~ number of cycles is 5 to 15 times longer than the purging time of the oxidants in the ~~fourth step in following~~ cycles after the initial number of cycles.

3. (Currently Amended) The method for manufacturing a semiconductor device according to claim 1, wherein ~~either~~ the second insulating film is selected from the group consisting of HfO_2, $HfAlO_x$, $HfSiO_x$, ~~or a nitride~~ and nitrides thereof ~~is used as the second insulating film~~.

4. (Currently Amended) The method for manufacturing a semiconductor device according to claim 1, wherein the initial ~~predetermined~~ number of cycles is 10 to 20 cycles.

5. (Currently Amended) A method for manufacturing a semiconductor device comprising ~~the steps of~~:

forming a first insulating film on a substrate;

forming a second insulating film on the first insulating film; and

forming a gate electrode on the second insulating film~~;~~, wherein

~~the step of~~ forming a second insulating film comprises

~~a first step of~~ supplying film-forming materials and ~~making~~ adsorbing the film-forming materials ~~adsorbed~~ on the first insulating film;

~~a second step of~~ purging the film-forming materials that ~~has~~ have not been adsorbed;

~~a third step of~~ supplying oxidants to oxidize the adsorbed film-forming materials; and

~~a fourth step of~~ purging the oxidants that ~~has~~ have not contributed to oxidization;

~~the step of~~ forming ~~a~~ the second insulating film ~~is repeated~~ repeatedly, for a plurality of cycles, continuously; and

~~the~~ purging the film-forming materials for a purging time ~~in the second step~~ in ~~the~~ an initial ~~predetermined~~ number of the plurality cycles that is ~~made~~ longer than the purging time of the film-forming materials in the ~~second step in following~~ cycles after the initial number of cycles.

6. (Currently Amended) The method for manufacturing a semiconductor device according to claim 5, wherein the purging time of the film-forming materials in the ~~second step in~~ initial ~~predetermined~~ number of cycles is 5 to 10 times longer than the purging time of the film-forming materials in the ~~second step in following~~ cycles after the initial number of cycles.

7. (Currently Amended) The method for manufacturing a semiconductor device according to claim 5, wherein ~~either~~ the second insulating film is selected from the group consisting of HfO_2, $HfAlO_x$, $HfSiO_x$, ~~or a nitride~~ and nitrides thereof ~~is used as the second insulating film~~.

8. (Currently Amended) The method for manufacturing a semiconductor device according to claim 5, wherein the initial ~~predetermined~~ number of cycles is 5 to 20 cycles.

9. (Currently Amended) A method for manufacturing a semiconductor device comprising ~~the steps of~~:

forming a first insulating film on a substrate;

forming a second insulating film on the first insulating film; and

forming a gate electrode on the second insulating film~~,~~, wherein

~~the step of~~ forming a second insulating film comprises

~~a first step of~~ supplying film-forming materials and ~~making~~ adsorbing the film-forming materials ~~adsorbed~~ on the first insulating film;

~~a second step of~~ purging the film-forming materials that ~~has~~ have not been adsorbed;

~~a third step of~~ supplying oxidants to oxidize the adsorbed film-forming materials; and

~~a fourth step of~~ purging the oxidants that ~~has~~ have not contributed to oxidization;

~~the step of~~ forming ~~a~~ the second insulating film ~~is repeated~~ repeatedly, for a plurality of cycles, continuously;

~~the~~ purging film-forming material for a purging time ~~in the second step~~ in ~~the~~ initial ~~predetermined~~ number of the plurality cycles that is ~~made~~ longer than the purging time in the ~~second step in following~~ cycles after the initial number of cycles for film-forming materials; and

~~the~~ purging the film-forming materials for a purging time ~~in the second step~~ in ~~the~~ an initial ~~predetermined~~ number of the plurality cycles that is ~~made~~ longer than the purging time the film-forming materials in the ~~second step in following~~ cycles after the initial number of cycles.

10. (Currently Amended) The method for manufacturing a semiconductor device according to claim 9, wherein

the purging time of the oxidants in the ~~fourth step in~~ initial ~~predetermined~~ number of cycles is 5 to 15 times longer than the purging time of the oxidants in the ~~fourth step in following~~ cycles after the initial number of cycles; and

the purging time of the film-forming materials in the ~~second step in~~ initial ~~predetermined~~ number of cycles is 5 to 10 times longer than the purging time of the film-forming materials in the ~~second step in following~~ cycles after the initial number of cycles.

11. (Currently Amended) The method for manufacturing a semiconductor device according to claim 9, wherein ~~either~~ the second insulating film is selected from the group consisting of HfO_2, $HfAlO_x$, $HfSiO_x$, ~~or a nitride~~ and nitrides thereof ~~is used as the second insulating film~~.

12. (Currently Amended) The method for manufacturing a semiconductor device according to claim 9, wherein the initial ~~predetermined~~ number of cycles is 10 to 20 cycles.

13. (Currently Amended) A method for manufacturing a semiconductor device comprising ~~the steps of~~:

forming a first insulating film on a substrate;

forming a second insulating film on the first insulating film; and

forming a gate electrode on the second insulating film~~,~~ wherein

~~the step of~~ forming a second insulating film comprises

~~a first step of~~ supplying film-forming materials and ~~making~~ adsorbing the film-forming materials ~~adsorbed~~ on the first insulating film;

~~a second step of~~ purging the film-forming materials that ~~has~~ have not been adsorbed;

~~a third step of~~ supplying oxidants to oxidize the adsorbed film-forming materials; and

~~a fourth step of~~ purging the oxidants that ~~has~~ have not contributed to oxidization;

~~the step of~~ forming ~~a~~ the second insulating film ~~is repeated~~ repeatedly, for a plurality of cycles, continuously; and

~~the supply~~ supplying a larger quantity of the oxidants ~~in the third step~~ in ~~the~~ an initial ~~predetermined~~ number of the plurality of cycles ~~is made more than the supply quantity of the oxidants in the third step~~ than in ~~following~~ the cycles after the initial number of cycles.

14. (Currently Amended) The method for manufacturing a semiconductor device according to claim 13, wherein the ~~supply~~ quantity of the oxidants ~~in the third step~~ supplied in the initial ~~predetermined~~ number of cycles is ~~made~~ 2 to 3 times ~~more~~ larger than the ~~supply~~ quantity of the oxidants ~~in the third step~~ supplied in ~~following~~ the cycles after the initial number of cycles.

15. (Currently Amended) The method for manufacturing a semiconductor device according to claim 13, wherein ~~either~~ the second insulating film is selected from the group consisting of HfO_2, $HfAlO_x$, $HfSiO_x$, ~~or a nitride~~ and nitrides thereof ~~is used as the second insulating film~~.

16. (Currently Amended) The method for manufacturing a semiconductor device according to claim 13, wherein the initial ~~predetermined~~ number of cycles is 5 to 20 cycles.

17. Currently Amended) A method for manufacturing a semiconductor device comprising ~~the steps of~~:

forming a first insulating film on a substrate;

forming a second insulating film on the first insulating film; and

forming a gate electrode on the second insulating film~~;~~, wherein

~~the step of~~ forming a second insulating film comprises

~~a first step of~~ supplying film-forming materials and ~~making~~ adsorbing the film-forming materials ~~adsorbed~~ on the first insulating film;

~~a second step of~~ purging the film-forming materials that ~~has~~ have not been adsorbed;

~~a third step of~~ supplying oxidants to oxidize the adsorbed film-forming materials; and

~~a fourth step of~~ purging the oxidants that ~~has~~ have not contributed to oxidization;

~~the step of~~ forming ~~a~~ the second insulating film ~~is~~ repeated for a plurality of cycles continuously;

~~the supply of~~ supplying the oxidants ~~in the third step is separated to~~ a plurality of separated times; and

~~the number of times for~~ supplying the oxidants ~~in the third step~~ in ~~the~~ an initial ~~predetermined~~ number of the plurality of cycles ~~is made more than the~~ a number of the separated times larger in number than the number of separated times ~~for supplying~~ of supplying the oxidants in the ~~third step in following~~ cycles following the initial number of cycles.

18. (Currently Amended) The method for manufacturing a semiconductor device according to claim 17, wherein the number of the separated times ~~for~~ of supplying the oxidants ~~in the third step~~ in the initial ~~predetermined~~ number of cycles is ~~made~~ 2 to 3 times

~~more~~ larger than the number of the separated times ~~for~~ of supplying the oxidants in the ~~third step in following~~ cycles following the initial number of cycles.

19. (Currently Amended) The method for manufacturing a semiconductor device according to claim 17, wherein ~~either~~ the second insulating film is selected from the group consisting of HfO_2, $HfAlO_x$, $HfSiO_x$, ~~or a nitride~~ and nitrides thereof ~~is used as the second insulating film~~.

20. (Currently Amended) The method for manufacturing a semiconductor device according to claim 17, wherein the initial ~~predetermined~~ number of cycles is 5 to 20 cycles.